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Crystallite phase and orientation determinations of (Mn,Ga)As/GaAscrystallites using analyzed (precession) electron diffraction patterns



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- 1. Material system: (Mn,Ga)As/GaAs-crystallites
- 2. Structure analysis using

Nano-beam Diffraction (NBD) Precession Electron Diffraction Technique (PED)

- \rightarrow Structure type I + II
- 3. Phase and orientation mapping using ASTAR
- 4. Conclusion





Motivation

- α-MnAs: ferromagnetic properties (Curie temperature above room temp.)
- combination of α-MnAs and paramagnetic semiconductor materials (e.g. GaAs) for spintronic devices
- \rightarrow fast **information transport** basing on the intrinsic electron spin

Growth process



- Metal-organic chemical vapor deposition (MOCVD)
- [001]-oriented GaAs substrate
- Deposition of Ga, Mn and As at 870K
- Formation of **crystallites during cooling** process























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[100]













Instrumentation









HAADF STEM















Assumption: Statistically distribution of Manganese atoms (75%) and Gallium atoms (25%) at cation positions

 α -Mn_{0.75}Ga_{0.25}As

hexagonal Space group: P6₃/mmc

Short: α–**Mn**_{0.75}**Ga**_{0.25}**As (hex)**





orthorhombic Space group: Pnma

Short: β-Mn_{0.75}Ga_{0.25}As (orth)







Structure analysis of Mn_{0.75}Ga_{0.25}As Nano-beam electron diffraction





Nano-beam mode Spot size: 1.0 nm



Templates









Structure analysis of Mn_{0.75}Ga_{0.25}As Nano-beam electron diffraction





Nano-beam mode Spot size: 1.0 nm



Templates









Reflection conditions (kinematic)



Hexagonal	Reflection conditions*		α-(Mn,Ga)As
$P6_3/mmc$	General:	×	
No. 194 P 6 ₃ /m 2/m 2/c	$hh\overline{2hl}: l = 2n$ $000l : l = 2n$	0001 0003 000(2n-1)	$\frac{1}{1}$
Orthorhomb	ic		β-(Mn,Ga)As
ormonionio	General:	×	
Pnma	0kl : $k+l=2n$	100	F++
No. 62	hk0: h=2n	300	
$P 2_1/n 2_1/m 2_1/a$	h00: h = 2n 0k0: k = 2n	 (2n-1)00	T T

* International Tables for Crystallography: Volume A – space group symmetry; ed. Th. Hahn



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Kinematic Electron Diffraction:

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- Only single scattering processes take place
- No double diffraction
- Each individual diffraction event acts independently of the others
- Two-beam condition (just the undiffracted beam and one diffracted beam are only excited)

Very thin crystals

Dynamic Electron Diffraction:



- Interaction of waves
- Multiple scattering effects
- Double diffraction possible (strong reflections behave like new primary beams)
- Dynamical effects increase with the number of excited reflections

Thick crystals







- Tilting the incident electron beam away from the zone axis (tilting angle = **precession angle** ε , typically 1°-3°)
 - → less beams are simultaneously excited
- Continuous integration of the reflections over the entire range of angle ω



Precession Electron Diffraction (PED) chwuchs kademie





precession angle : 0,00 deg $\varepsilon = 0^{\circ}$ $\varepsilon = 3.26^{\circ}$ 5 1/nm 5 1/nm

Advantages:

- Symmetrical precession patterns are obtained also for off-zone orientation tilted by less than 1°
- Dynamical effects are reduced due to the off-axis beam inclinations because less beams are simultaneously excited
- The number of reflections is higher electron conventional than in diffraction

chwuchs Kademie Iwissenschaft und Stitechnik Precession Electron Diffraction (PED)





 $\varepsilon = 3.26^{\circ}$

5 1/nm

 $\varepsilon = 0^{\circ}$

5 1/nm



JEOL JEM 2200 FS Unprecessed: 1nm Precessed (ε=1°): 10nm

Problems:

- The loss of the spatial resolution (depends on the precession angle and spherical aberation)
- Overlaps between Laue zones are possible for high precession angles
- Information about the shape of the reflections is lost by integration over ω
- Reflections at low angle stay in Bragg condition for longer time than reflections at high angles (Lorentz effect)









Structure analysis of (Mn,Ga)As



Nano-beam mode, spot size: 1.0 nm Precession OFF Precession ON: 0.96°









Simulation Precession ON: 0.95°

Precession angle: 0,95 deg											Thickness:					100	nm			
ZA: [0 21 22]																				
				•		•	•	•		•	•	•		•						
					٠				•		٠		٠		٠					
	۰		٠	٠	٠	٠	٠	•	٠	٠	٠	٠	٠	٠	٠		۰			
							•	٠	۰	•	•									
-Mn _{0.75} Ga	^a 0.2	₅ A Pn	s	2 (th.	or	ho	122	hi	.)									



Structure analysis of (Mn,Ga)As



Nano-beam mode, spot size: 1.0 nm Precession **OFF** Precession ON: 0.96° As Crystallite A Crystallite A Mn 75%, Ga 25% Crystallite B **Crystallite B** ✓ Superlattice reflections **Modification of structure**

Assumption: Superstructure

Each second cation lattice plane of the superlattice is completely occupied with Manganese atoms. 50% of Manganese and 50% of Gallium are statistically distributed on the other cation lattice planes.

Mn_{0.75}Ga_{0.25}As Superstructure Type II







Structure analysis of (Mn,Ga)As















Phases of Mn_{0.75}Ga_{0.25}As







Phases of Mn_{0.75}Ga_{0.25}As













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Materials analysis:

- Chemical composition of crystallites as found by EDXS: $Mn_{0.75}Ga_{0.25}As$
- Formation of **superstructure** in $Mn_{0.75}Ga_{0.25}As$ as revealed by PED
- **Proposal of structure models** of a trigonal phase (derived from the hexagonal α -phase of Mn_{0.75}Ga_{0.25}As) and of a monoclinic phase (derived from the orthorhombic β -phase of Mn_{0.75}Ga_{0.25}As)
- Phase and orientation mapping
 - Identification of **two phases** within the crystallites: monoclinic β -Mn_{0.75}Ga_{0.25}As hexagonal α -Mn_{0.75}Ga_{0.25}As
 - Oriented growth of (Mn,Ga)As with respect to the GaAs matrix
 - Multi-grain growth found for individual crystallites







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NanoMEGAS company

Financial support : Deutsche Forschungsgemeinschaft (DFG)





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